

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	426	((thin adj film adj stack) OR FILM)near8 MEMS	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 13:15	
2	BRS	L2	2173	359/290-298.CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 13:15	
3	BRS	L3	19	1 AND 2	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 13:15	
4	BRS	L4	2846	430/319,320,321.CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 13:16	
5	BRS	L5	3	1 AND 4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 13:16	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
6	BRS	L6	32612	427/162-248.1.CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 13:17	
7	BRS	L7	6	1 AND 6	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 13:17	
8	BRS	L8	12530	((microelectromechanical adj system) or MEMS)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 13:18	
9	BRS	L9	142479	etch\$ and pattern\$3 and deposit\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 13:19	
10	BRS	L10	3999	8 and 9	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 13:19	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
11	BRS	L11	8	10 and (metal) and (conductive adj oxide or oxide) and (fluoride) and (silicide) and (polymer)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT	2004/09/1 4 13:20	
12	BRS	L12	862	216/2.ccls.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT	2004/09/1 4 13:21	
13	BRS	L14	1	11 and 12	USPA T; US-P GPUB ; EPO; JPO; DERW ENT	2004/09/1 4 13:21	